

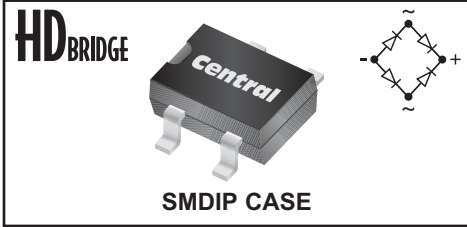
CBRSDSH2-100
SURFACE MOUNT
HIGH DENSITY
2 AMP SILICON
SCHOTTKY BRIDGE RECTIFIER



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CBRSDSH2-100 is a full wave bridge rectifier mounted in a durable epoxy surface mount case, utilizing glass passivated chips.



MARKING: FULL PART NUMBER

FEATURES:

- High 2.0A Current Rating
- Low V_F Schottky Diodes (700mV MAX @ $I_F=2.0A$)

MAXIMUM RATINGS: ($T_A=25^\circ C$ unless otherwise noted)

	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	100	V
DC Blocking Voltage	V_R	100	V
RMS Reverse Voltage	$V_{R(RMS)}$	70	V
Average Forward Current ($T_A=75^\circ C$)	I_O	2.0	A
Peak Forward Surge Current (8.3ms)	I_{FSM}	110	A
Operating Junction Temperature	T_J	-50 to +125	$^\circ C$
Storage Temperature	T_{stg}	-50 to +150	$^\circ C$

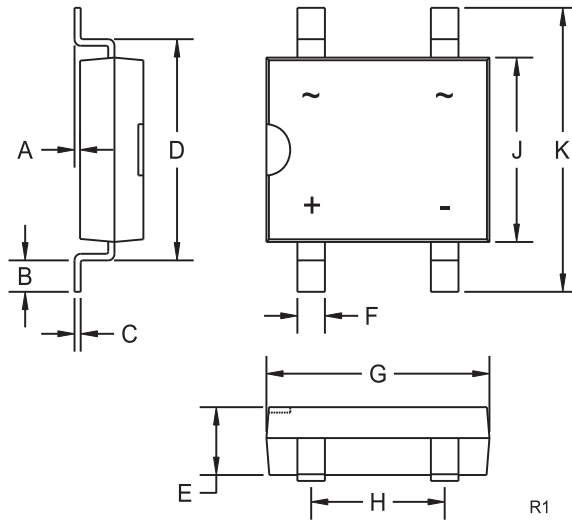
ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^\circ C$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	TYP	MAX	UNITS
I_R	$V_R=100V$	1.0	50	μA
V_F	$I_F=2.0A$	650	700	mV
C_J	$V_R=4.0V, f=1.0MHz$	280	500	pF

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SMDIP CASE - MECHANICAL OUTLINE



DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.008	0.10	0.20
B	0.040	0.060	1.02	1.52
C	0.009		0.23	
D	0.290	0.310	7.37	7.87
E	0.086	0.098	2.18	2.49
F	0.038	0.042	0.97	1.07
G	0.316	0.335	8.03	8.51
H	0.195	0.205	4.95	5.21
J	0.245	0.255	6.22	6.48
K	0.360	0.410	9.14	10.41

SMDIP (REV: R1)

MARKING: FULL PART NUMBER

R2 (14-December 2011)